

ABSTRACT OF THE DISCLOSURE

An insulated gate bipolar transistor includes a first semiconductor layer of a first conductivity type, a second semiconductor layer of a second conductivity type formed on a top surface of the first semiconductor layer, a base layer of the first conductivity type formed on a top surface of the second semiconductor layer, a plurality of gate electrodes each of which is buried in a trench with a gate insulation film interposed therebetween, the trench being formed in the base layer to a depth reaching said second semiconductor layer from a surface of the base layer, each the gate electrode having an upper surface of a rectangular pattern with different widths in two orthogonal directions, the gate electrodes being disposed in a direction along a short side of the rectangular pattern, and emitter layers of the second conductivity type formed in the surface of the base layer to oppose both end portions of each the gate electrode in a direction along a long side of the rectangular pattern.